

BCP52-16

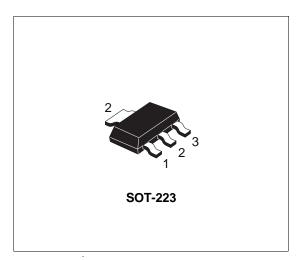
LOW POWER PNP TRANSISTOR

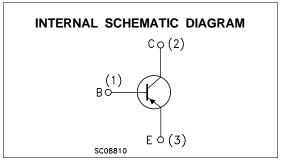
Ordering Code	Marking		
BCP52-16	BCP5216		

- SILICON EPITAXIAL PLANAR PNP MEDIUM VOLTAGE TRANSISTOR
- SOT-223 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE NPN COMPLEMENTARY TYPE IS BCP55-16

APPLICATIONS

- MEDIUM VOLTAGE LOAD SWITCH TRANSISTORS
- OUTPUT STAGE FOR AUDIO AMPLIFIERS CIRCUITS
- AUTOMOTIVE POST-VOLTAGE REGULATION





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage (I _E = 0)	-60	V	
V _{CEO}	Collector-Emitter Voltage (I _B = 0)	-60	V	
V_{CER}	Collector-Emitter Voltage ($R_{BE} = 1K\Omega$)	-60	V	
V _{EBO}	Emitter-Base Voltage $(I_C = 0)$	-5	V	
Ι _C	Collector Current	-1	A	
ICM	Collector Peak Current (t _p < 5 ms)	-1.5	A	
I _B	Base Current	-0.1	A	
I _{BM}	Base Peak Current (t _p < 5 ms)	-0.2	A	
P _{tot}	Total Dissipation at T _{amb} = 25 °C	1.4	W	
T _{stg}	Storage Temperature	-65 to 150	°C	
Tj	Max. Operating Junction Temperature	150	°C	

September 2003

THERMAL DATA

R _{thj-amb} •	Thermal Resistance Junction-Ambient	Max	89.3	°C/W
 Device moun 	ted on a PCB area of 1 cm ²			

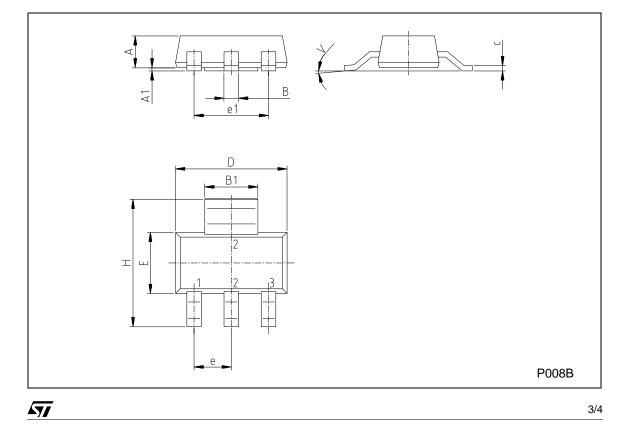
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Ісво	Collector Cut-off Current (I _E = 0)	$V_{CB} = -30 V$ $V_{CB} = -30 V$ $T_j = 125 \ ^{o}C$			-100 -10	nA μA
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C = -100 μA	-60			V
V _{(BR)CEO*}	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = -20 mA	-60			V
V _(BR) CER	Collector-Emitter Breakdown Voltage (R _{BE} = 1 KΩ)	I _C = -100 μA	-60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = -10 μA	-5			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$I_{\rm C} = -500 \text{ mA}$ $I_{\rm B} = -50 \text{ mA}$			-0.5	V
$V_{BE(on)}*$	Base-Emitter On Voltage	$I_{C} = -500 \text{ mA}$ $V_{CE} = -2 \text{ V}$			-1	V
h _{FE} *	DC Current Gain		40 100 25		250	
f _T	Transition Frequency	$I_C = -10 \text{ mA} \text{ V}_{CE} = -5 \text{ V} \text{ f} = 20 \text{ MHz}$		50		MHz

 \ast Pulsed: Pulse duration = 300 $\mu s,$ duty cycle \leq 1.5 %

DIM.		mm			inch			
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А			1.80			0.071		
В	0.60	0.70	0.80	0.024	0.027	0.031		
B1	2.90	3.00	3.10	0.114	0.118	0.122		
С	0.24	0.26	0.32	0.009	0.010	0.013		
D	6.30	6.50	6.70	0.248	0.256	0.264		
е		2.30			0.090			
e1		4.60			0.181			
E	3.30	3.50	3.70	0.130	0.138	0.146		
Н	6.70	7.00	7.30	0.264	0.276	0.287		
V			10 [°]			10 [°]		
A1		0.02						





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